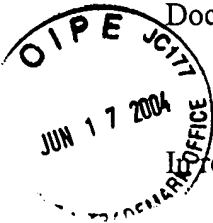


IFW

Docket No.: 60188-807

PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor Application of	:	Customer Number: 20277
	:	
Osamu KUSUMOTO, et al.	:	Confirmation Number: 4190
	:	
Serial No.: 10/801,606	:	Group Art Unit: 2811
	:	
Filed: March 17, 2004	:	Examiner:
	:	
For: SILICON CARBIDE SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME		

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the document listed on the attached form PTO-1449. It is respectfully requested that the document be expressly considered during the prosecution of this application, and that the document be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/801,606

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.


Respectfully submitted,

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Date: June 17, 2004

<div>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</div> <div></div> <div>(PTO-1449)</div>		ATTY. DOCKET NO. 60188-807		SERIAL NO. 10/801,606			
		APPLICANT Osamu KUSUMOTO, et al.					
		FILING DATE March 17, 2004		GROUP 2811			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		PARTIAL ENGLISH TRANSLATION OF: Toshiyuki OHNO, "Recent Progress in SiC-Based Device Processing", Journal of Institute of Electronics, Information and Communication Engineers, pp. 128-133, Vol. J81-C-II, No. 1, January 1998, Japan					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.